What is claimed is:

1. A light-emitting device comprising:

a first passivation film and a second passivation film; and

a light-emitting element formed between the first passivation film and the second passivation film,

wherein the light-emitting element comprises an anode, a cathode and a light-emitting layer between the anode and the cathode;

wherein the light-emitting layer comprises a dopant at a concentration of 0.1 % by weight or more and 0.4 % by weight or less.

2. A light-emitting device comprising:

a first passivation film and a second passivation film;

a photosensitive organic resin film having an opening; and

a light-emitting element having an anode, a cathode and a light-emitting layer between the anode and the cathode,

wherein the light-emitting layer comprises a dopant at a concentration of 0.1 % by weight or more and 0.4 % by weight or less;

wherein the anode and the photosensitive organic resin film are formed on the first passivation film;

wherein the anode, the cathode and the light-emitting layer are overlapped in the opening,

wherein the photosensitive organic resin film and the cathode are covered with the second passivation film.

3. A light-emitting device according to claim 2, wherein a radius of curvature of a curve that a section in the opening of the photosensitive organic resin film depicts is in the range of from 0.2 to 2 μm.

4. A light-emitting device according to claim 2, wherein the photosensitive

organic resin film has positive photosensitivity.

5. A light-emitting device according to claim 2, wherein the photosensitive organic resin film has negative photosensitivity.

6. A light-emitting device according to any one of claims 1 and 2, wherein at least one of the first passivation film and the second passivation film is a carbon nitride film or a silicon nitride film formed by an RF sputtering process.

7. A light-emitting device according to any one of claims 1 and 2, wherein at least one of the first passivation film and the second passivation film comprises a material selected from the group consisting of DLC, boron nitride and alumina.

8. A light-emitting device as according to any one of claim 1 and 2,

wherein the light-emitting device includes a transistor that controls a current that is supplied to the light-emitting element, and

wherein the transistor is operated in a saturation region.

9. A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting element, after turning on for 100 hr with an initial intrinsic brightness set at 320 cd/mm^2 and a duty ratio set at 70 %, has a diminishing amount of the intrinsic brightness of substantially 10 % or less of the initial intrinsic brightness.

10. A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting element, after turning on for 1000 hr with an initial intrinsic brightness set at 320 cd/mm^2 and a duty ratio set at 70 %, has a diminishing amount of the intrinsic brightness of substantially 20 % or less of the initial intrinsic brightness.

11. A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting device includes a transistor that controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate, and

wherein when brightness of the light-emitting element is set at 200 nt when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 40 degree centigrade or less.

12. A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting device includes a transistor that controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate,

wherein when power consumption of the light-emitting element and the transistor is set at 600 mW when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 40 degree centigrade or less.

13. A light-emitting device as set forth in any one of claims 1 through 8:

wherein the light-emitting device includes a transistor that controls a current that is supplied to the light-emitting element;

both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device; and

the pixel portion is disposed on a substrate;

wherein when brightness of the light-emitting element is set at 130 nt when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 35 degree centigrade or less.

14. A light-emitting device according to any one of claims 1 and 2,

wherein the light-emitting device includes a transistor that controls a current that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate, and

wherein when power consumption of the light-emitting element and the transistor is set at 400 mW when a duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion of the substrate is 35 degree centigrade or less.

15. A light-emitting device according to any one of claims 1 and 2, wherein the light-emitting layer comprises a quinacridone derivative.

16. A method of manufacturing a light-emitting device that includes an anode, a cathode and a light-emitting element disposed between the anode and the cathode, comprising:

forming the anode on a first passivation film;

forming a photosensitive organic resin film over the anode;

forming an opening partially in the photosensitive organic resin film by exposure so that the anode is partially exposed;

heating the organic resin film under a vacuum atmosphere;

forming a light-emitting layer having a dopant concentration of 0.1 % by weight or more and 0.4 % by weight or less over the organic resin film and the anode;

forming the cathode over the light-emitting layer so that the anode, the cathode and the light-emitting layer are overlapped in the opening; and

forming a second passivation film over the organic resin film and the cathode.

17. A method of manufacturing a light-emitting device according to claim 16, wherein the vacuum atmosphere is a vacuum of 3×10^{-7} Torr or less.

18. A method of manufacturing a light-emitting device according to claim 16, wherein at least one of the first passivation film and the second passivation film is a carbon nitride film or a silicon nitride film deposited by an RF sputtering process.

19. A method of manufacturing a light-emitting device according to claim 16, wherein at least one of the first passivation film and the second passivation film comprises a material selected from the group consisting of DLC, boron nitride and alumina.

20. A method of manufacturing a light-emitting device according to claim 16, wherein a radius of curvature of a curve that a section in the opening of the organic resin film depicts is in the range of from 0.2 to 2 μm.

21. A method of manufacturing a light-emitting device according to claim 16, wherein the organic resin film has positive photosensitivity.

22. A method of manufacturing a light-emitting device according to claim 16, wherein the organic resin film has negative photosensitivity.